**Pb Free Product** 



# **NCE N-Channel Super Trench Power MOSFET**

#### **Description**

The NCEP85T12 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

#### **General Features**

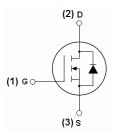
- $V_{DS}$  =85V, $I_{D}$  =120A  $R_{DS(ON)}$  <5.3m $\Omega$  @  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

## **Application**

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

100% ΔVds TESTED!



#### Schematic diagram



#### Marking and pin assignment



TO-220-3L top view

## **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP85T12	NCEP85T12	TO-220-3L	-	-	-

### Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	85	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	I <sub>D</sub>	120	Α
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	88	Α
Pulsed Drain Current	I <sub>DM</sub>	320	Α
Maximum Power Dissipation	P <sub>D</sub>	160	W
Derating factor		1.1	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	784	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 175	$^{\circ}$ C



# http://www.ncepower.com

# NCEP85T12

## **Thermal Characteristic**

Thermal Resistance, Junction-to-Case (Note 2)	R <sub>eJC</sub>	0.94	°C/W
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**Electrical Characteristics (T<sub>C</sub>=25**°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	- '		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =85V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	2.5	-	4.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =60A	-	4.5	5.3	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =10V,I <sub>D</sub> =60A	40	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	\/ -40\/\/ -0\/	-	5500	-	PF
Output Capacitance	Coss	$V_{DS}$ =40V, $V_{GS}$ =0V, F=1.0MHz	-	830	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UIVID2	-	57	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	13.5	-	nS
Turn-on Rise Time	t <sub>r</sub>	V <sub>DD</sub> =40V,I <sub>D</sub> =60A	-	12.5	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10 $V$ , $R_{G}$ =4.7 $\Omega$	-	38	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	13.5	-	nS
Total Gate Charge	Qg	V -40V/1 -60A	-	55		nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =40V, $I_{D}$ =60A, $V_{GS}$ =10V	-	21		nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> -10V	-	9		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =120A	-		1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	120	Α
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = I <sub>S</sub>	-	74		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	176		nC

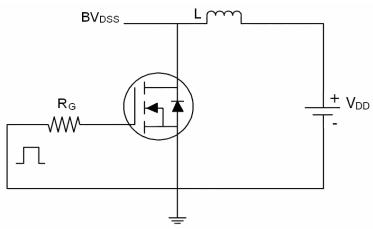
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,V\_DD=42.5V,V\_G=10V,L=0.5mH,Rg=25 $\Omega$

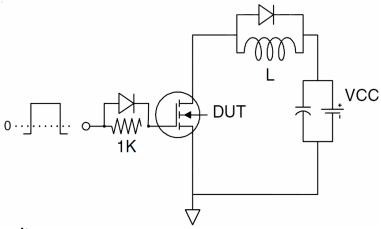


## **Test Circuit**

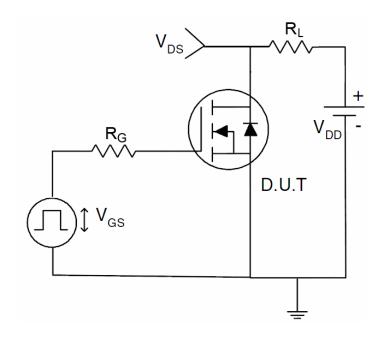
# 1) E<sub>AS</sub> test Circuit



## 2) Gate charge test Circuit

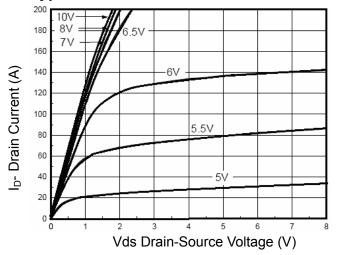


# 3) Switch Time Test Circuit

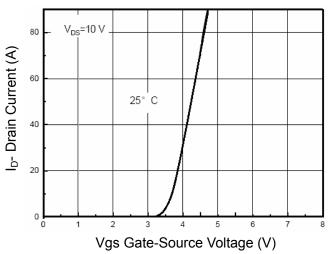




## **Typical Electrical and Thermal Characteristics**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

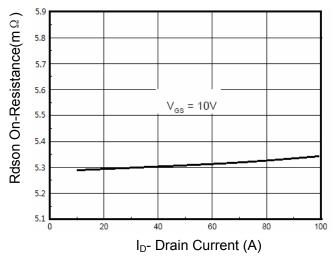


Figure 3 Rdson- Drain Current

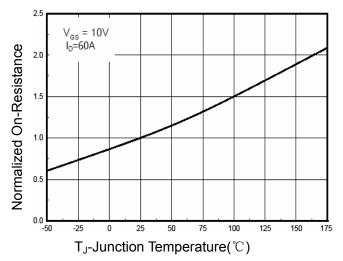


Figure 4 Rdson-JunctionTemperature

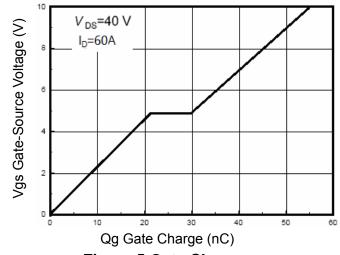


Figure 5 Gate Charge

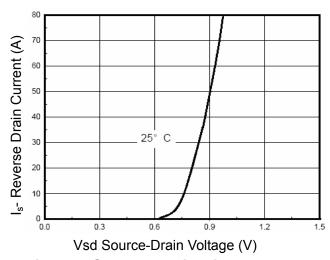


Figure 6 Source- Drain Diode Forward



C Capacitance (pF)

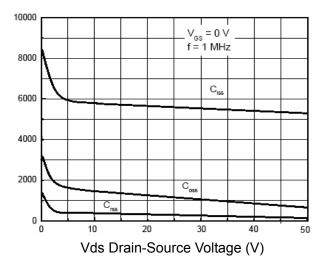


Figure 7 Capacitance vs Vds

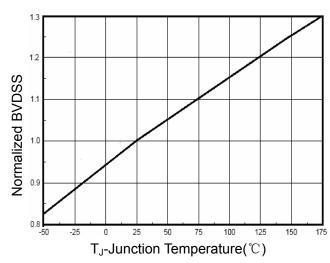
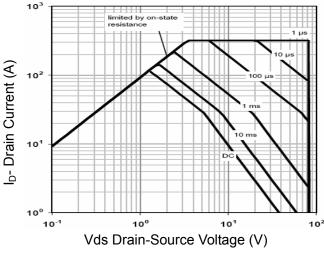
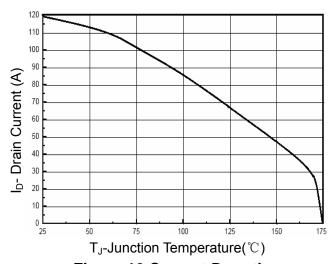


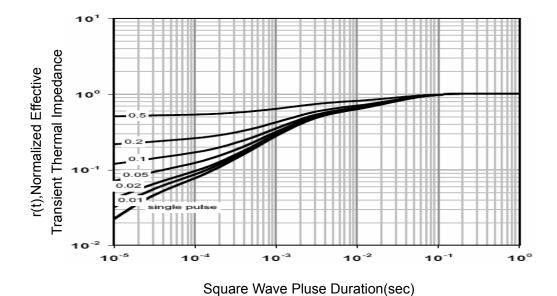
Figure 9 BV<sub>DSS</sub> vs Junction Temperature



**Figure 8 Safe Operation Area** 



**Figure 10 Current De-rating** 

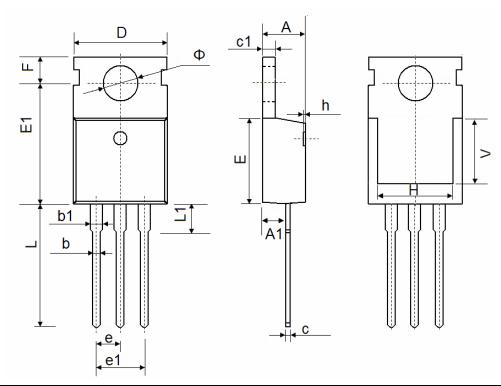


**Figure 11 Normalized Maximum Transient Thermal Impedance** 

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# NCEP85T12

# **TO-220-3L Package Information**



Symbol	Dimensions	In Millimeters	Dimensions In Inches			
	Min.	Max.	Min.	Max.		
А	4.400	4.600	0.173	0.181		
A1	2.250	2.550	0.089	0.100		
b	0.710	0.910	0.028	0.036		
b1	1.170	1.370	0.046	0.054		
С	0.330	0.650	0.013	0.026		
c1	1.200	1.400	0.047	0.055		
D	9.910	10.250	0.390	0.404		
E	8.9500	9.750	0.352	0.384		
E1	12.650	12.950	0.498	0.510		
е	2.54	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204		
F	2.650	2.950	0.104	0.116		
Н	7.900	8.100	0.311	0.319		
h	0.000	0.300	0.000	0.012		
L	12.900	13.400	0.508	0.528		
L1	2.850	3.250	0.112	0.128		
V	7.500 REF.		0.295 REF.			
Ф	3.400	3.800	0.134	0.150		



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